

General Description

The MY7N65D is silicon N-channel Enhanced VDMOSFETS, obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy.

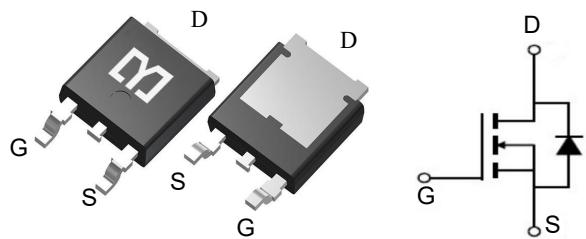


Features

V _{DSS}	650	V
I _D	7	A
P _D (T _C = 25 °C)	38	W
R _{DS(ON)} (at V _{GS} = 10V)	< 1.4	Ω

Application

- High efficiency switch mode power supplies
- Power factor correction
- Electronic lamp ballast



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY7N65D	TO-252	MY7N65D	1000

Absolute Maximum Ratings (T_c=25 °C unless otherwise noted)

Symbol	Parameters	Ratings	Unit
V _{DSS}	Drain-Source Voltage	650	V
V _{GS}	Gate-Source Voltage-Continuous	±30	V
I _D	Drain Current-Continuous (Note 2)	7	A
I _{DM}	Drain Current-Single Plused (Note 1)	28	A
P _D	Power Dissipation (Note 2)	38	W
T _j	Max.Operating junction temperature	150	°C/W

Electrical Characteristics ($T_c=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
Static Characteristics						
B_{VDSS}	Drain-Source Breakdown VoltageCurrent (Note 1)	650	--	--	mA	$I_D=250\mu\text{A}$ $V_{GS}=0\text{V}$, $T_J=25^\circ\text{C}$
$V_{GS(\text{th})}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$
$R_{DS(\text{on})}$	Drain-Source On-Resistance	--	1.2	1.4	Ω	$V_{GS}=10\text{V}$, $I_D=3.5\text{A}$
I_{GSS}	Gate-Body Leakage Current	--	--	± 100	nA	$V_{GS}=\pm 30\text{V}$, $V_{DS}=0$
I_{DSS}	Zero Gate Voltage Drain Current	--	--	1	μA	$V_{DS}=650\text{V}$, $V_{GS}=0$
g_{fs}	Forward Transconductance	2.3	--	--	S	$V_{DS}=15\text{V}$, $I_D=3.5\text{A}$
Switching Characteristics						
$T_{d(\text{on})}$	Turn-On Delay Time	--	48	80	ns	$V_{DS}=325\text{V}$, $I_D=7\text{A}$, $R_G=25\Omega$ (Note 2)
T_r	Rise Time	--	135	170	ns	
$T_{d(\text{off})}$	Turn-Off Delay Time	--	135	175	ns	
T_f	Fall Time	--	280	320	ns	
Q_g	Total Gate Charge	--	30	65	nC	$V_{DS}=520$, $V_{GS}=10\text{V}$, $I_D=7\text{A}$ (Note 2)
Q_{gs}	Gate-Source Charge	--	6.5	--	nC	
Q_{gd}	Gate-Drain Charge	--	13.5	--	nC	
Dynamic Characteristics						
C_{iss}	Input Capacitance	--	1080	1690	pF	$V_{DS}=25\text{V}$, $V_{GS}=0$, $f=1\text{MHz}$
C_{oss}	Output Capacitance	--	118	200	pF	
C_{rss}	Reverse Transfer Capacitance	--	30	45	pF	
I_s	Continuous Drain-Source Diode Forward Current (Note 2)	--	--	7	A	
V_{SD}	Diode Forward On-Voltage	--	--	1.4	V	$I_s=7\text{A}$, $V_{GS}=0$
$R_{th(j-c)}$	Thermal Resistance, Junction to Case	--	--	2.6	$^\circ\text{C}/\text{W}$	

Note 1: Repetitive Rating : Pulse width limited by maximum junction temperature

Note 2: Pulse test: PW <= 300us , duty cycle <= 2%.

Ratings and Characteristic curves

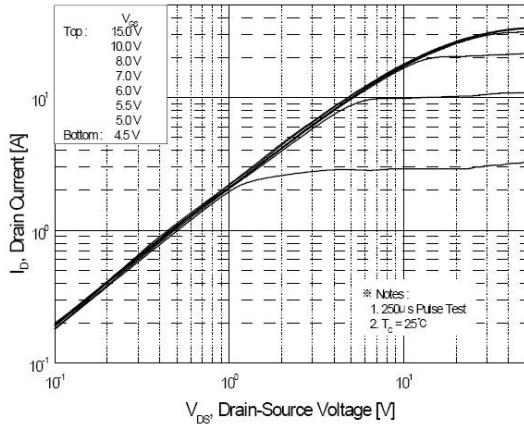


Figure 1. On-Region Characteristics

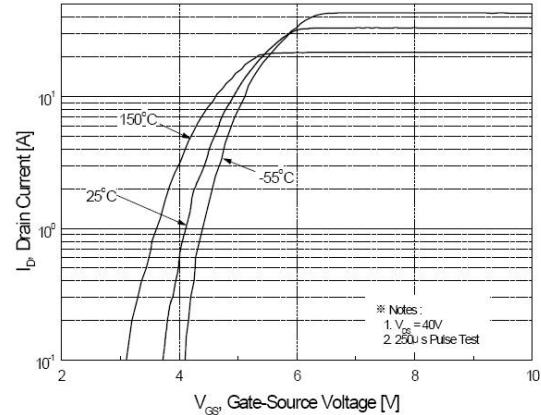


Figure 2. Transfer Characteristics

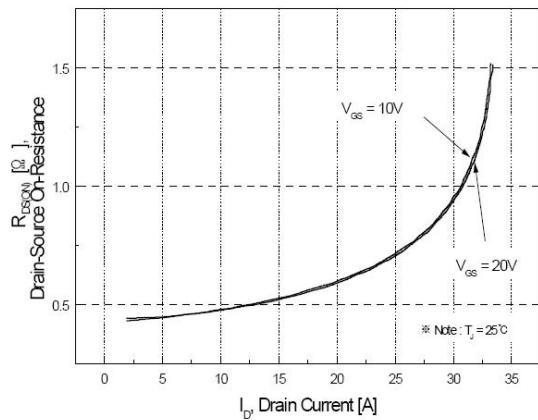


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

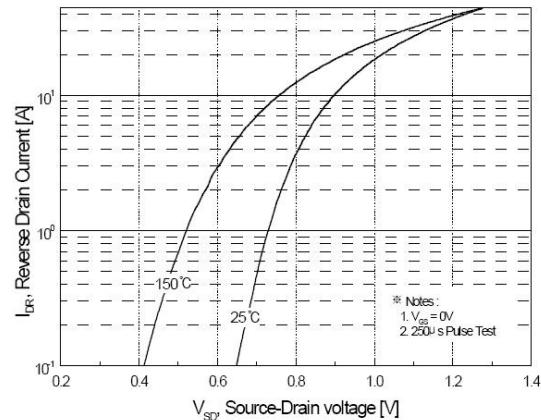


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

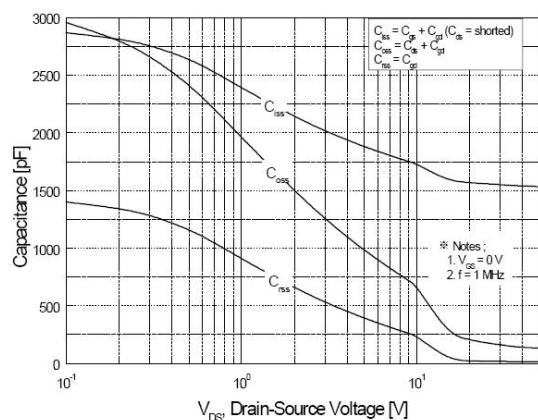


Figure 5. Capacitance Characteristics

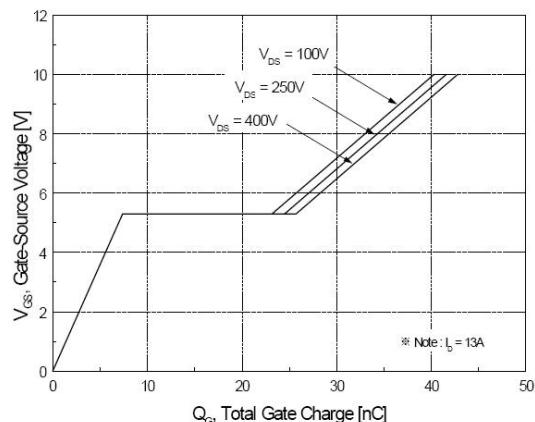


Figure 6. Gate Charge Characteristics

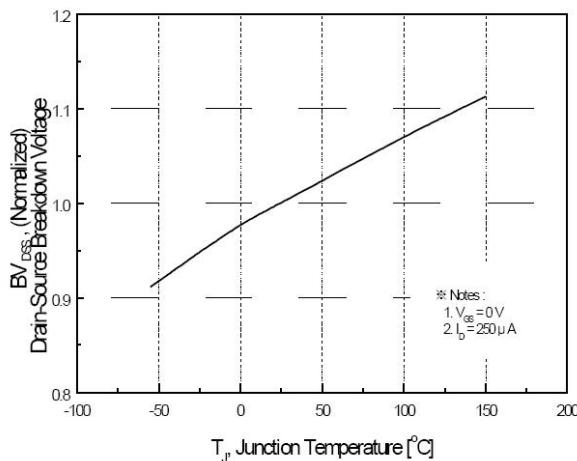


Figure 7. Breakdown Voltage Variation vs Temperature

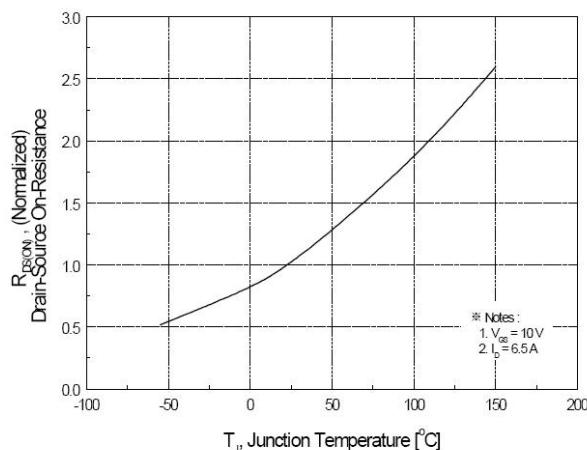


Figure 8. On-Resistance Variation vs Temperature

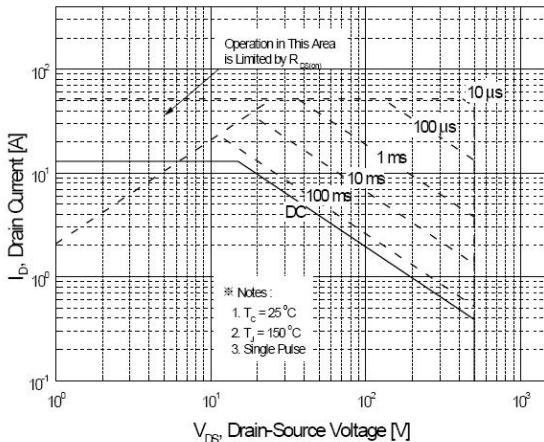


Figure 9. Maximum Safe Operating Area

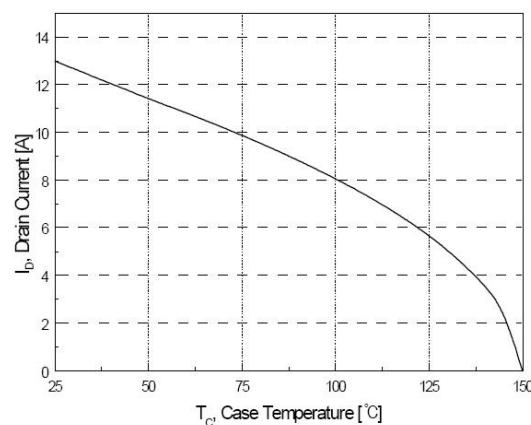


Figure 10. Maximum Drain Current vs Case Temperature

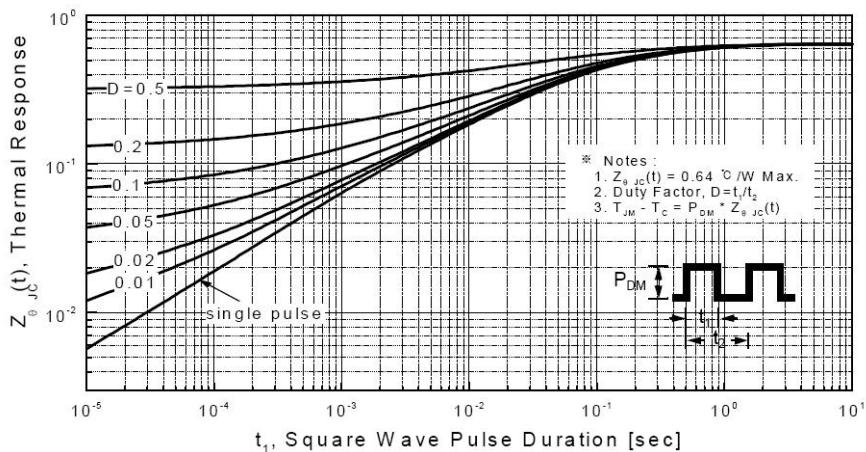


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform

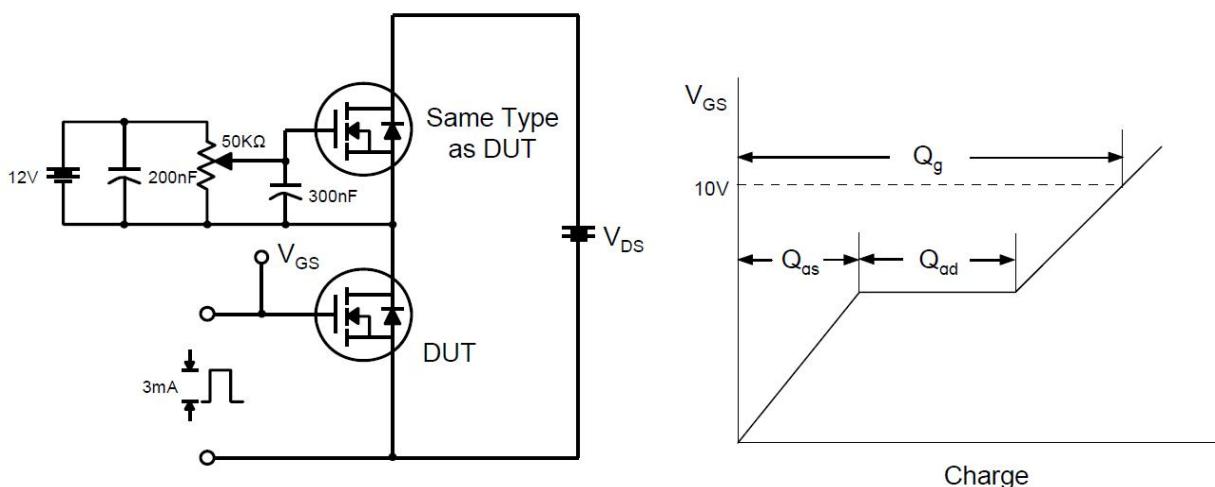


Fig 13. Resistive Switching Test Circuit & Waveforms

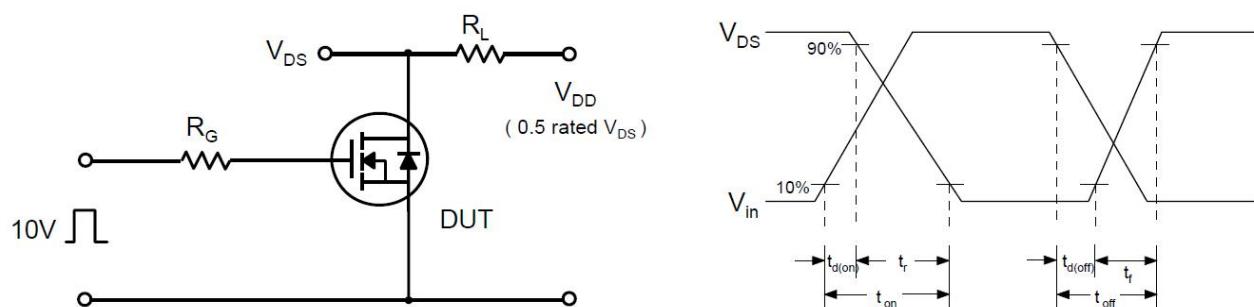


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

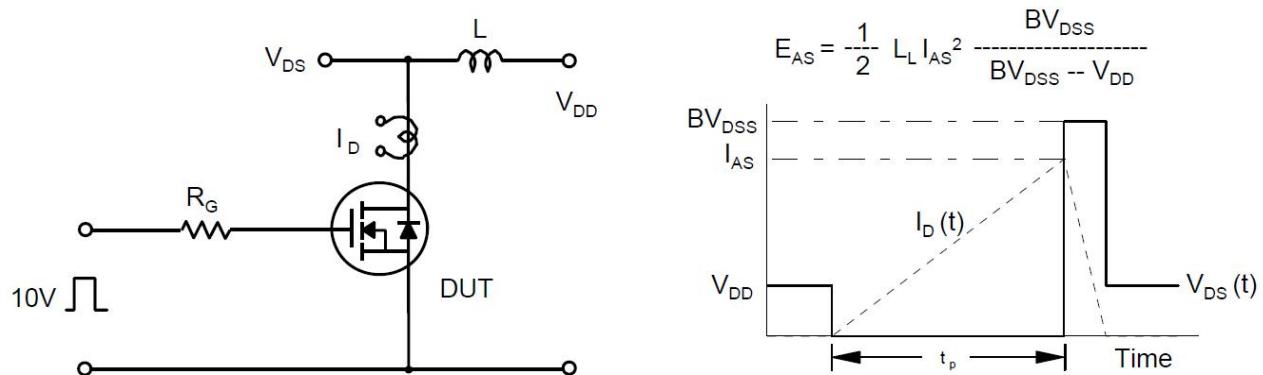
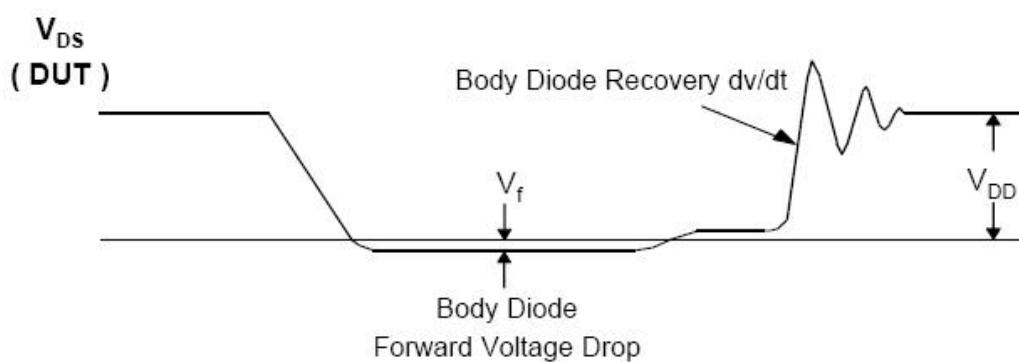
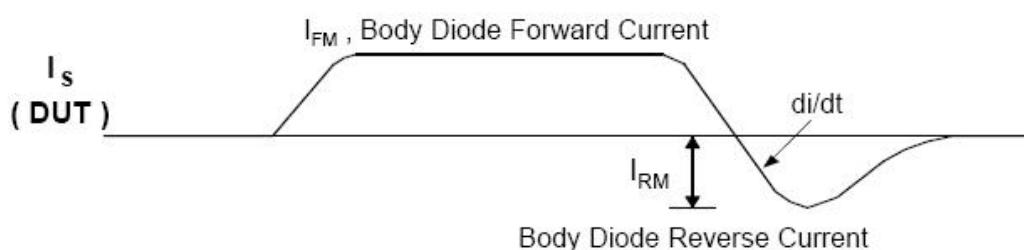
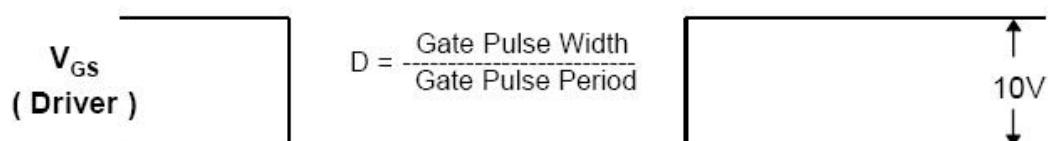
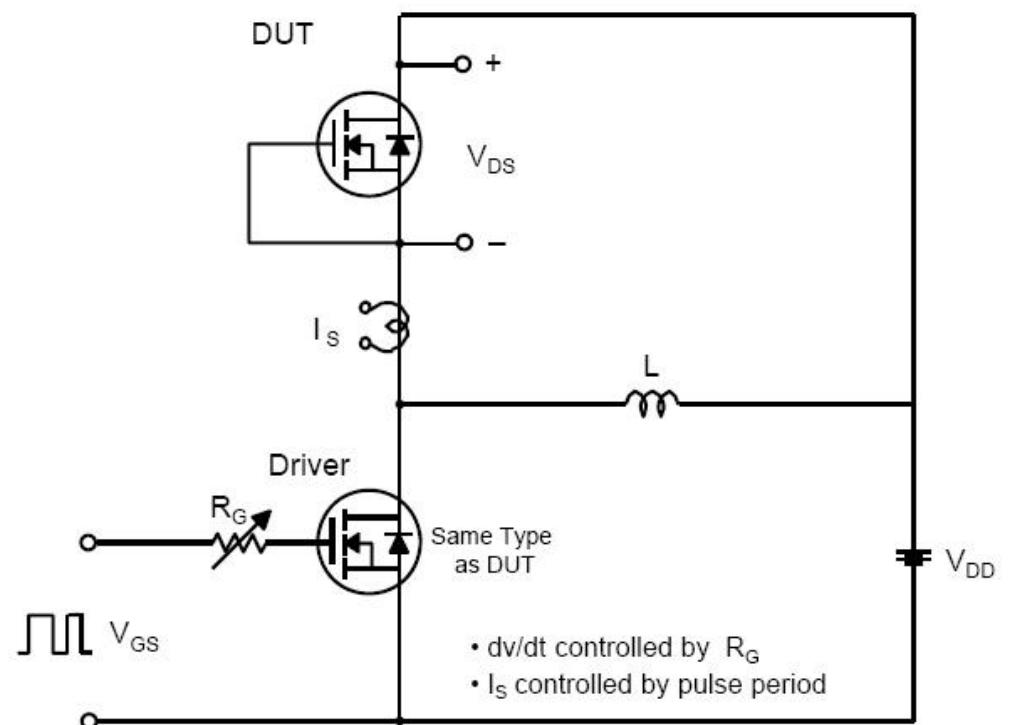
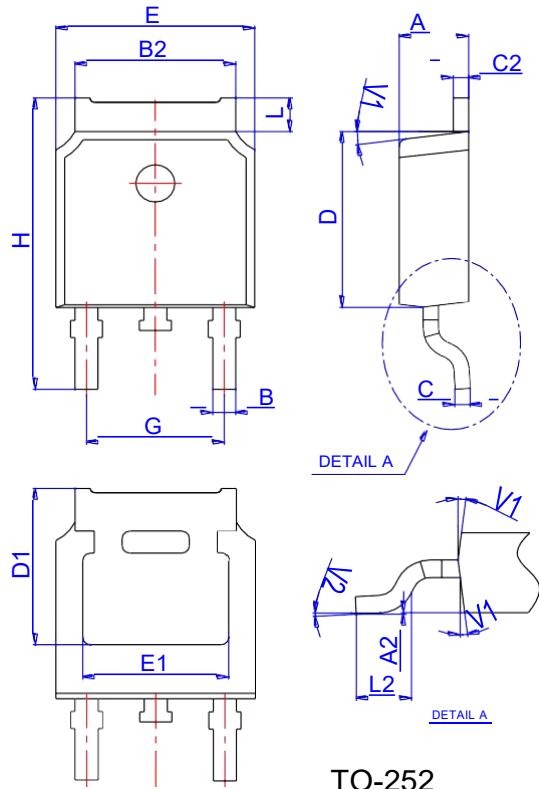


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



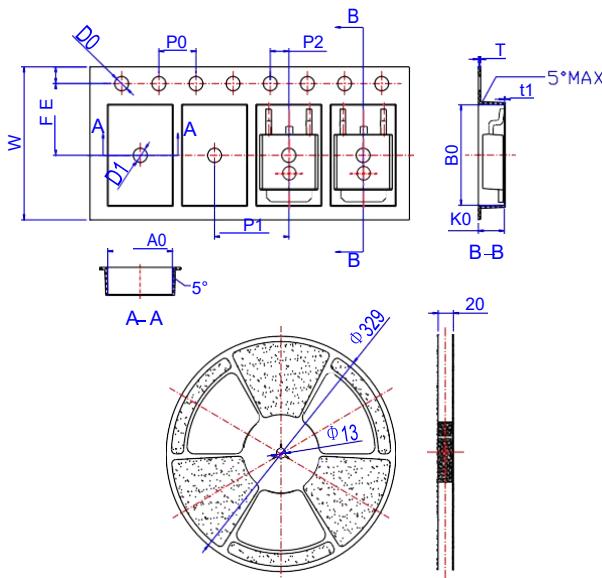
Package Mechanical Data-TO-252-JQ Single



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10			2.50	0.083	
A2	0			0.10	0	
B	0.66			0.86	0.026	
B2	5.18			5.48	0.202	
C	0.40			0.60	0.016	
C2	0.44			0.58	0.017	
D	5.90			6.30	0.232	
D1	5.30REF			0.209REF		
E	6.40			6.80	0.252	
E1	4.63				0.182	
G	4.47			4.67	0.176	
H	9.50			10.70	0.374	
L	1.09			1.21	0.043	
L2	1.35			1.65	0.053	
V1		7°				7°
V2	0°			6°	0°	6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24			0.027	0.009	
t1	0.10				0.004	
10P0	39.80	40.00	40.20	1.567	1.575	1.583